

**INFORMATION DISCLOSURE
CITATION FORM FOR
PATENT APPLICATION
(FORM PTO-1449)
(Substitute)**

Docket No.: YOR920030208US1

Serial No.: 10/699226

Applicant(s): Hyungjun KIM et al.

Filing Date:

Group: 1762

U.S. PATENTS

Initials	Patent Number	Issue Date	Name	Class	Sub-class	Filing date

FOREIGN PATENT DOCUMENTS

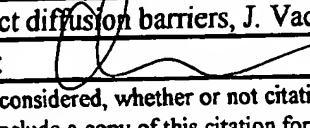
Initials	Document Number	Date	Country	Name	Translation? Yes/No/n/a

OTHER DOCUMENTS (Title, Author, Date, Pages, Etc., if known)

Kim et al., Diffusion barrier properties of transition metal thin films grown by plasma-enhanced atomic layer deposition, J. Vac. Sci. Technol. B 20(4), J/A 2002 pp 1321-1326

Kim et al., Growth kinetics and initial stage growth during plasma-enhanced Ti atomic layer deposition, J. Vac. Sci. Technol. A 20(3), May/June 2002 PP 802-808

Rossnagel et al., Plasma-enhanced atomic layer deposition of Ta and Ti for interconnect diffusion barriers, J. Vac. Sci. Technol. B 18(4), July/Aug 2002 pp 2016-2020

Examiner's Signature: 

Date Considered: 9/04/05

Initial if reference was considered, whether or not citation is in conformance with MPEP. Mark through citation if not considered.

Include a copy of this citation form with your next correspondence to the Applicant(s).

INFORMATION DISCLOSURE STATEMENT BY THIRD-PARTY

(Multiple sheets used when necessary)

Application No. 10/699,226
 Filing Date October 31, 2003
 First Named Inventor Kim
 Art Unit 1775-1762
 Examiner ~~Turner, Archeno A.~~ Chen
 Attorney Docket No.

JUN 13 2005

SHEET 1 OF 1

U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
		2004/0009307 A1	01-15-2004	Koh et al.	

FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No.	Foreign Patent Document Country Code-Number-Kind Code Example: JP 1234567 A1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T ¹

NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ¹
		Atomic Layer Deposition (ALD) 2002 American Vacuum Society Topical Conference, August 19-21, 2002, Hanyang University, Korea, Program Schedule and Content.	
		H. KIM & S.M. ROSSNAGEL, "The Growth and Properties of PE-ALD Ta and TaN Thin Films" (Invited lecture), Atomic Layer Deposition (ALD) 2002 American Vacuum Society Topical Conference, August 19-21, 2002, Hanyang University, Korea, Abstract.	
		H. KIM & S.M. ROSSNAGEL, "The Growth and Properties of PE-ALD Ta and TaN Thin Films" (Invited lecture), Atomic Layer Deposition (ALD) 2002 American Vacuum Society Topical Conference, August 19-21, 2002, Hanyang University, Korea, Presentation Slided.	

1722785_1
060705

Examiner Signature	Date Considered
	9/4/05

*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

T¹ - Place a check mark in this area when an English language Translation is attached.